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Page 1 of 5

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List of Pat	ents and Publ	ications	Statement	Appl	icants:				
(Use seve	ral sheets if no	ecessar	y)	Disne					
					p Date: mber 25, 2003				
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				Filing Date:	2002				
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ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18 Stylesheet Version v18.0

> Title of Invention

Method of Fabricating a High-Voltage Transistor With A Multi-Layered Extended Drain Structure

Application Number:

10/722792

Confirmation Number:

7244

First Named Applicant:

Donald Disney

Attorney Docket Number: 03692.P059DC

Art Unit:

2818

David Nhu

Examiner:

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or 6525372 or 6468847 or 5973360 or 5637898 . or 5665994 or 4929987 or 4531173 or 6573558 or 6555873 or 6509220 or 6667213 or 6635544 or 6365932 or 4626789 or 6294818 or 5760440 or 6049108 or 5821144 or 4738936 or 5869875 or 6191447 or 4343015 or 6388286 or 6194283 or 4890144 or 6353252 or 6207994 or 5155574 or 5146298 or 4811075 or 4626879 or 4890146 or 5237193 or 5368136 or 5313082 or 5068700 or 5258636 or 20020175351 or 20020056884 or

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Signature

Examiner Name	Date	
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